

Form 1449*	Docket Number: G&C 30794.79-US-U1	Application Number: 09/922,122
Applicant: Hugues Marchand et al.		
Filing Date: August 3, 2001		Group Art Unit: 1765


U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M>	5,880,485	03/09/99	Marx et al.			
	6,153,010	11/28/00	Kiyoku et al.			
	6,180,270	01/30/01	Cole et al.			
	6,291,319	09/18/01	Yu et al.			
	6,328,796	12/11/01	Kub et al.			
	6,358,770	03/19/02	Itoh et al.			
	6,391,748	05/21/02	Temkin et al.			
	6,420,197	07/16/02	Ishida et al.			
	6,440,823	08/27/02	Vaudo et al.			
	6,459,712	10/01/02	Tanaka et al.			
	6,524,932	02/25/03	Zhang et al.			
	6,548,333	04/15/03	Smith			
	6,610,144	08/26/03	Mishra et al.			
	6,707,074	03/16/04	Yoshii et al.			
M>	6,765,240	07/20/04	Tischler et al.			

FOREIGN PATENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

NON-PATENT DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
M>		Bykhovski, A.D. et al., "Elastic strain relaxation in GaN-AlN-GaN semiconductor - insulator - semiconductor structures," J. Appl. Phys. 78(6):3691-3696, September 15, 1995
M>		Dadgar, A. et al., "Metalorganic Chemical Vapor Phase Epitaxy of Crack-Free GaN on Si (111) Exceeding 1µm in Thickness," Jpn. J. Appl. Phys. 39:L1183-1185, November 15, 2000
M>		Lei, T. et al., "Epitaxial growth of zinc blende and wurtzitic gallium nitride thin films on (001) silicon," Appl. Phys. Lett. 59(8):944-946, August 19, 1991
M>		Guha, S. et al., "Ultraviolet and violet GaN light emitting diodes on silicon," Appl. Phys. Lett. 72(4):415-417, January 26, 1998

EXAMINER: <i>Matt S</i>	DATE CONSIDERED: <i>7/18/2005</i>
EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	

Form 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION	Docket Number: G&C 30794.79-US-U1	Application Number: 09/922,122
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	Haffouz, S. et al., "The effect of the Si/N treatment of a nitridated sapphire surface on the growth mode of GaN in low-pressure metalorganic vapor phase epitaxy," Applied Physics Letters, 73(9):1278-1280, August 31, 1998
	Lahrech, H. et al., "Optimisation of AlN and GaN growth by metalorganic vapour-phase epitaxy (MOVPE) on Si(111)," Journal of Crystal Growth, 217:13-25, 2000
	Nikishin, S.A. et al., "High quality GaN grown on Si(111) by gas source molecular beam epitaxy with ammonia," Applied Physics Letters, 75(14):2073-2075, October 4, 1999
	Semond, F. et al., "GaN grown on Si(111) substrate: From two-dimensional growth to quantum well assessment," Applied Physics Letters, 75(1):82-84, July 5, 1999
	Seon, M. et al., "Selective growth of high quality GaN on Si(111) substrates," Applied Physics Letters, 76(14):1842-1844, April 3, 2000
	Ohtani, A. et al., "Microstructure and photoluminescence of GaN grown on Si(111) by plasma-assisted molecular beam epitaxy," Appl. Phys. Lett. 65(1):61-63, July 4, 1994
	Osinsky, A. et al., "Visible-blind GaN Schottky barrier detectors grown on Si(111)," Applied Physics Letters, 72(5):551-553, February 2, 1998
	Tanaka, S. et al., "Defect structure in selective area growth GaN pyramid on (111)Si substrate," Applied Physics Letters, 76(19):2701-2703, May 8, 2000
	Tran, C.A. et al., "Growth of InGaN/GaN multiple-quantum-well blue light-emitting diodes on silicon by metalorganic vapor phase epitaxy," Applied Physics Letters, 75(11):1494-1496, September 13, 1999
	Zhao, G.Y. et al., "Growth of Si delta-doped GaN by metalorganic chemical-vapor deposition," Applied Physics Letters, 77(14):2195-2197, October 2, 2000
M	Zhao, Z.M. et al., "Metal-semiconductor-metal GaN ultraviolet photodetectors on Si(111)," Applied Physics Letters, 77(3):444-446, July 17, 2000

EXAMINER: <i>Mart</i>	DATE CONSIDERED: 7/11/2005
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